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16-bit Buffers / Line Drivers with 3-state Outputs



ADE-205-119B(Z)

3rd Edition December 1996

Description

The HD74LVC16244A has sixteen line drivers with three state outputs in a 48 pin package. This device is a non inverting buffer and has two active low enables $(1\overline{G} \text{ to } 4\overline{G})$. Each enable independently controls four buffers. Low voltage and high speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- $V_{cc} = 2.0 \text{ V to } 5.5 \text{ V}$
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- All outputs V_{OUT} (Max.) = 5.5 V (@ V_{CC} = 0 V or output off state)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 24 mA (@V_{cc} = 3.0 V to 5.5 V)

Function Table

G	A	Output Y
Н	X	Z
L	Н	Н
L	L	L

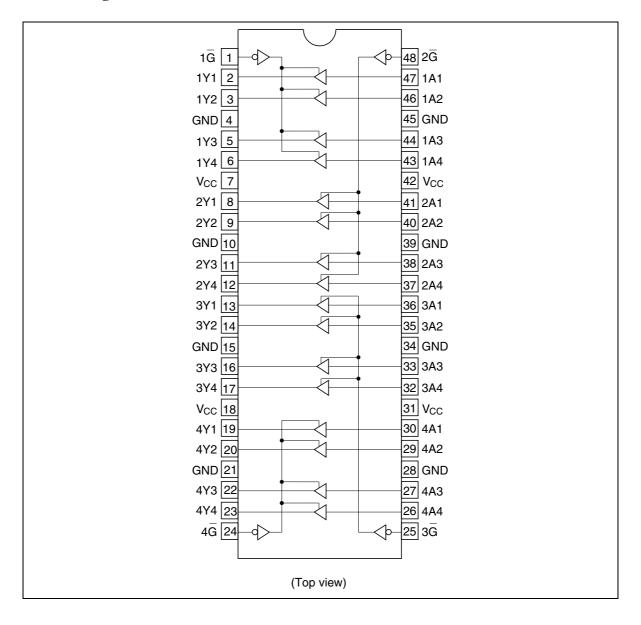
H: High level

L: Low level

X: Immaterial

Z: High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	-0.5 to 6.0	V	
Input diode current	I _{IK}	– 50	mA	V ₁ = -0.5 V
Input voltage	V _i	-0.5 to 6.0	V	
Output diode current	I _{ok}	– 50	mA	V ₀ = -0.5 V
		50	mA	$V_{o} = V_{cc} + 0.5 \text{ V}$
Output voltage	V _o	-0.5 to V_{cc} +0.5	V	Output "H" or "L"
		-0.5 to 6.0	V	Output "Z" or V _{cc} :OFF
Output current	I _o	±50	mA	
V _{cc} , GND current / pin	I _{CC} or I _{GND}	100	mA	
Storage temperature	Tstg	-65 to +150	°C	

Note: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	1.5 to 5.5	V	Data hold
		2.0 to 5.5	V	At operation
Input / output voltage	V _i	0 to 5.5	V	G, A
	V _o	0 to V _{cc}	V	Output "H" or "L"
		0 to 5.5	V	Output "Z" or V _{cc} :OFF
Operating temperature	Та	-40 to 85	°C	
Output current	I _{OH}	-12	mA	$V_{cc} = 2.7 \text{ V}$
		-24 ^{*2}	mA	V _{cc} = 3.0 V to 5.5 V
	I _{OL}	12	mA	V _{cc} = 2.7 V
		24*2	mA	V _{cc} = 3.0 V to 5.5 V
Input rise / fall time *1	t _r , t _r	10	ns/V	

Notes: 1. This item guarantees maximum limit when one input switches.

Waveform: Refer to test circuit of switching characteristics.

2. duty cycle ≤ 50%

Electrical Characteristics

Ta =	-40	to	85°C	
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Item	Symbol	$V_{cc}(V)$	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.7 to 3.6	2.0	_	V	
		4.5 to 5.5	V _{cc} ×0.7	_	V	-
	V _{IL}	2.7 to 3.6	_	0.8	V	
		4.5 to 5.5	_	V _{cc} ×0.3	V	_
Output voltage	V _{OH}	2.7 to 5.5	V _{cc} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.7	2.2	_	V	$I_{OH} = -12 \text{ mA}$
		3.0	2.4	_	V	_
		3.0	2.2	_	V	I _{OH} = -24 mA
		4.5	3.8	_	V	_
	V _{OL}	2.7 to 5.5	_	0.2	٧	$I_{OL} = 100 \mu A$
		2.7	_	0.4	V	I _{OL} = 12 mA
		3.0	_	0.55	V	I _{OL} = 24 mA
		4.5	_	0.55	V	_
Input current	I _{IN}	0 to 5.5	_	±5.0	μΑ	V _{IN} = 5.5 V or GND
Off state output current	l _{oz}	2.7 to 5.5	_	±5.0	μА	$V_{IN} = V_{CC}$, GND $V_{OUT} = 5.5 \text{ V or GND}$
Output leak current	I _{OFF}	0	_	20	μΑ	$V_{IN}/V_{OUT} = 5.5 V$
Quiescent supply current	I _{cc}	2.7 to 3.6	_	±20	μΑ	$V_{IN} / V_{OUT} = 3.6 \text{ to } 5.5 \text{ V}$
		2.7 to 5.5	_	20	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{cc}	3.0 to 3.6	_	500	μΑ	V_{IN} = one input at(V_{CC} -0.6)V, other inputs at V_{CC} or GND

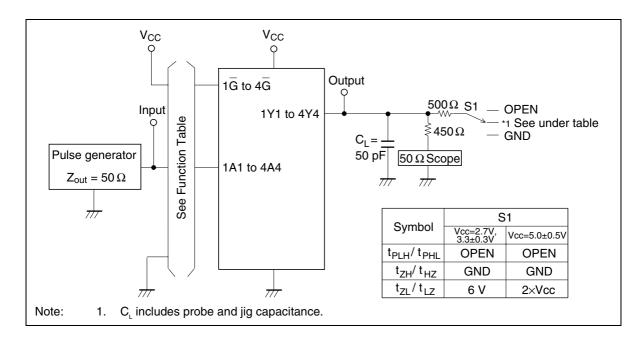
Switching Characteristics

		$Ta = -40 \text{ to } 85^{\circ}\text{C}$						
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	From (Input)	To (Output)
Propagation delay time	t _{plH}	2.7	_	_	5.8	ns	A	Υ
	$t_{_{PHL}}$	3.3±0.3	1.5	_	5.2	ns	_	
		5.0±0.5	_	_	4.0	ns	_	
Output enable time	t _{zн}	2.7	_	_	8.2	ns	G	Υ
	$\mathbf{t}_{_{\mathrm{ZL}}}$	3.3±0.3	1.5	_	7.5	ns	_	
		5.0±0.5	_	_	5.5	ns	_	
Output disable time	t _{HZ}	2.7	_	_	7.7	ns	G	Υ
	\mathbf{t}_{LZ}	3.3±0.3	1.5	_	7.0	ns	_	
		5.0±0.5	_	_	6.0	ns	_	
Between output pins skew *1	t _{oslh}	2.7	_	_	_	ns		
	$\mathbf{t}_{\scriptscriptstyle{OSHL}}$	3.3±0.3	_	_	1.0	ns	_	
		5.0±0.5		_	1.0	ns		
Input capacitance	C _{IN}	2.7	_	3.0	_	pF		
Output capacitance	C _o	2.7	_	15.0	_	pF		

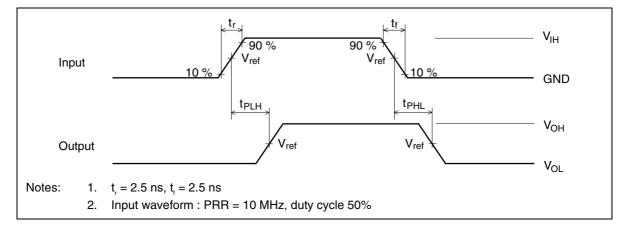
Note: 1. This parameter is characterized but not tested.

$$\mathsf{tos}_{\mathsf{LH}} = \mathsf{I} \; \mathsf{t}_{\mathsf{PLHm}} - \mathsf{t}_{\mathsf{PLHn}} \, \mathsf{I}, \, \mathsf{tos}_{\mathsf{HL}} = \mathsf{I} \; \mathsf{t}_{\mathsf{PHLm}} - \mathsf{t}_{\mathsf{PHLn}} \, \mathsf{I}$$

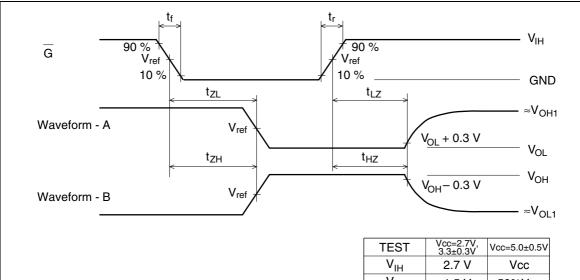
Test Circuit



Waveforms - 1



Waveforms - 2

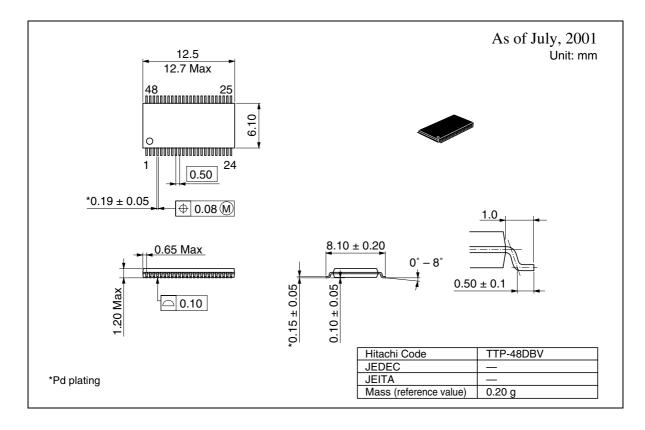


TEST	Vcc=2.7V, 3.3±0.3V	Vcc=5.0±0.5V
V _{IH}	2.7 V	Vcc
V _{ref}	1.5 V	50%Vcc
V _{OH1}	3 V	Vcc
V _{OL1}	GND	GND

Notes:

- 1. $t_r = 2.5 \text{ ns}, t_r = 2.5 \text{ ns}$
- 2. Input waveform: PRR = 10 MHz, duty cycle 50%
- 3. Waveform A shows input conditions such that the output is "L" level when enable by the output control.
- 4. Waveform B shows input conditions such that the output is "H" level when enable by the output control.

Package Dimensions



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